

Transistors

# Power Transistor (−80V, −1A)

## 2SB1260 / 2SB1181 / 2SB1241

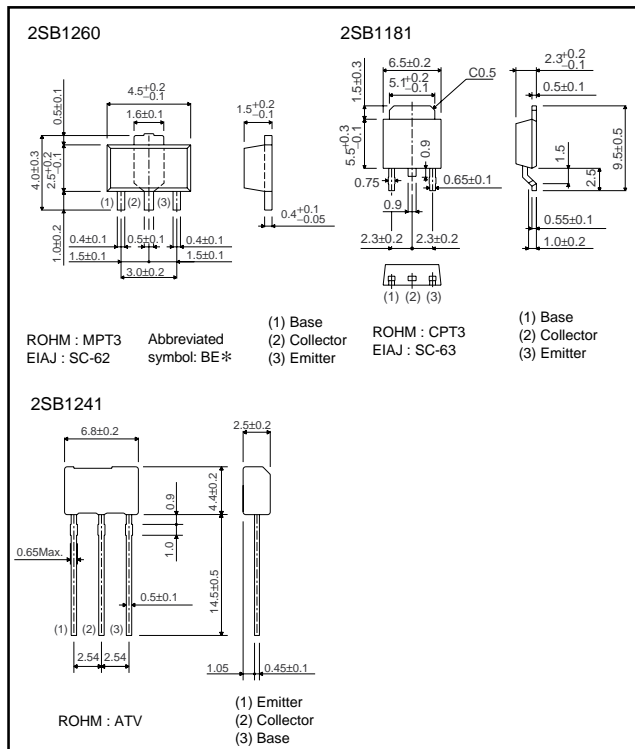
●Features

- 1) High breakdown voltage and high current.  
 $V_{CE0} = -80V$ ,  $I_c = -1A$
- 2) Good  $h_{FE}$  linearity.
- 3) Low  $V_{CE(sat)}$ .
- 4) Complements the 2SD1898 / 2SD1863 / 2SD1733.

●Structure

Epitaxial planar type  
 PNP silicon transistor

●External dimensions (Unit : mm)



\* Denotes  $h_{FE}$

●Absolute maximum ratings ( $T_a=25^\circ C$ )

| Parameter                   | Symbol           | Limits     | Unit       |
|-----------------------------|------------------|------------|------------|
| Collector-base voltage      | $V_{CBO}$        | -80        | V          |
| Collector-emitter voltage   | $V_{CEO}$        | -80        | V          |
| Emitter-base voltage        | $V_{EBO}$        | -5         | V          |
| Collector current           | $I_c$            | -1         | A (DC)     |
|                             | $I_{CP}$         | -2 *1      | A (Pulse)  |
| Collector power dissipation | 2SB1260          | 0.5        | W          |
|                             | 2SB1241, 2SB1181 | 2 *2       |            |
|                             | 2SB1181          | 1 *3       |            |
| Junction temperature        | $T_j$            | 150        | $^\circ C$ |
| Storage temperature         | $T_{stg}$        | -55 to 150 | $^\circ C$ |

\*1 2SB1260 :  $P_w=20ms$  duty=1/2  
 2SB1241 : Single pulse,  $P_w=100ms$

\*2 2SB1260 : When mounted on a 40x40x0.7 mm ceramic board.

\*3 2SB1241 : Printed circuit board, 1.7mm thick, collector copper plating 100mm<sup>2</sup> or larger.

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●Electrical characteristics (Ta=25°C)

| Parameter                            | Symbol               | Min.            | Typ. | Max. | Unit | Conditions                                     |  |
|--------------------------------------|----------------------|-----------------|------|------|------|--|--|
| Collector-base breakdown voltage     | BV <sub>CB0</sub>    | -80             | -    | -    | V    | I <sub>C</sub> = -50μA                         |  |
| Collector-emitter breakdown voltage  | BV <sub>CEO</sub>    | -80             | -    | -    | V    | I <sub>C</sub> = -1mA                          |  |
| Emitter-base breakdown voltage       | BV <sub>EB0</sub>    | -5              | -    | -    | V    | I <sub>E</sub> = -50μA                         |  |
| Collector cutoff current             | I <sub>CB0</sub>     | -               | -    | -1   | μA   | V <sub>CB</sub> = -60V                         |  |
| Emitter cutoff current               | I <sub>EB0</sub>     | -               | -    | -1   | μA   | V <sub>EB</sub> = -4V                          |  |
| Collector-emitter saturation voltage | V <sub>CE(sat)</sub> | -               | -    | -0.4 | V    | I <sub>C</sub> /I <sub>B</sub> = -500mA/ -50mA |  |
| DC current transfer ratio            | 2SB1260, 2SB1181     | h <sub>FE</sub> | 82   | -    | 390  | -  | V <sub>CE</sub> = -3V, I <sub>C</sub> = -0.1A          |
|                                      | 2SB1241              |                 | 120  | -    | 390  | -  |  |
| Transition frequency                 | 2SB1181              | f <sub>T</sub>  | -    | 100  | -    | MHz  | V <sub>CE</sub> = -10V, I <sub>E</sub> =50mA, f=100MHz |
| Output capacitance                   | 2SB1260              | C <sub>ob</sub> | -    | 20   | -    | pF   | V <sub>CB</sub> = -10V<br>I <sub>E</sub> =0A<br>f=1MHz |
|                                      | 2SB1181, 2SB1241     |                 | -    | 25   | -    | pF   |  |

●Packaging specifications and h<sub>FE</sub>

| Type    | h <sub>FE</sub> | Package                      | Taping |      |      |
|---------|-----------------|------------------------------|--------|------|------|
|         |                 | Code                         | TL     | TV2  | T100 |
|         |                 | Basic ordering unit (pieces) | 2500   | 2500 | 1000 |
| 2SB1260 | PQR             | -                            | -      | ○    |      |
| 2SB1241 | QR              | -                            | ○      | -    |      |
| 2SB1181 | PQR             | ○                            | -      | -    |      |

h<sub>FE</sub> values are classified as follows :

| Item            | P         | Q          | R          |
|-----------------|-----------|------------|------------|
| h <sub>FE</sub> | 82 to 180 | 120 to 270 | 180 to 390 |

●Electrical characteristic curves

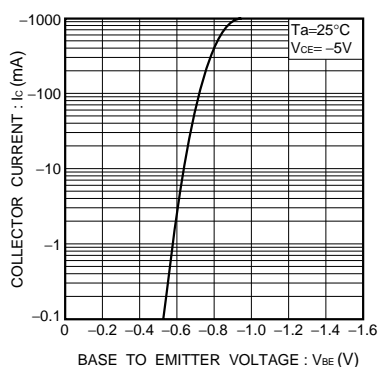


Fig.1 Grounded emitter propagation characteristics

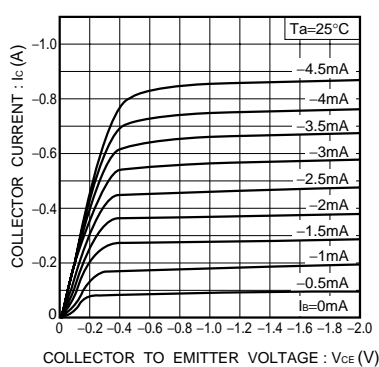


Fig.2 Grounded emitter output characteristics

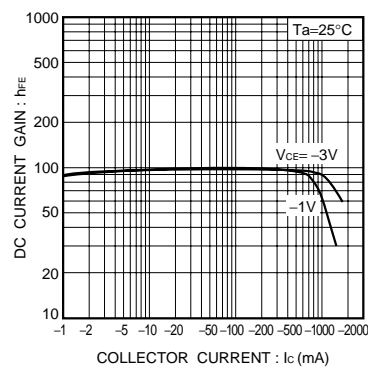


Fig.3 DC current gain vs. collector current

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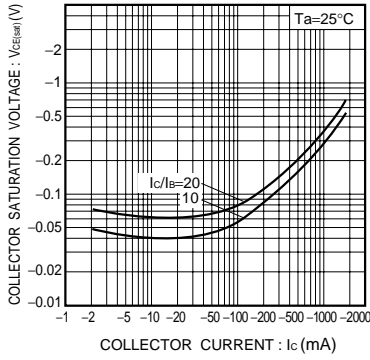


Fig.4 Collector-emitter saturation voltage vs. collector current

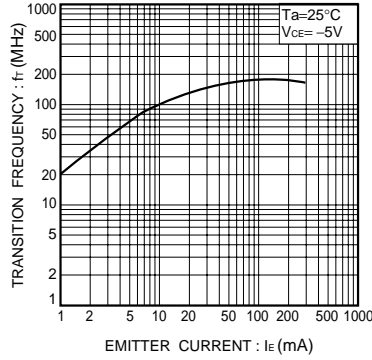


Fig.5 Gain bandwidth product vs. emitter current

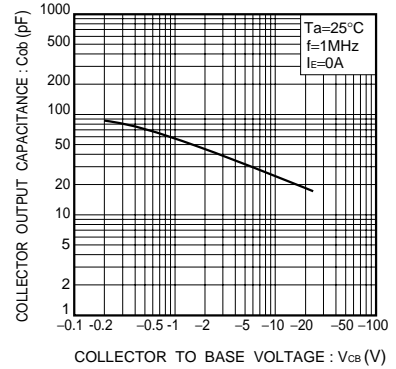


Fig.6 Collector output capacitance vs. collector-base voltage

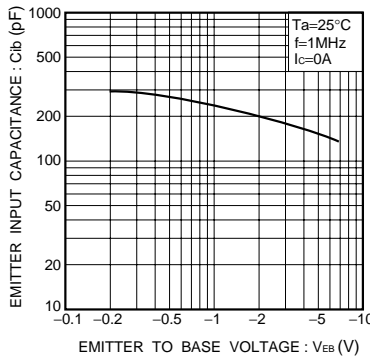


Fig.7 Emitter input capacitance vs. emitter-base voltage

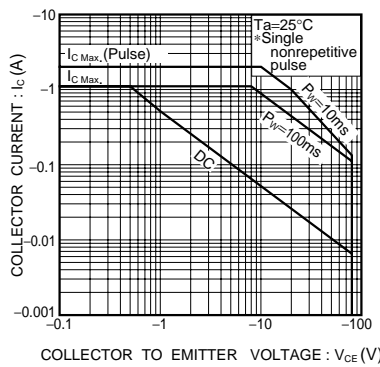


Fig.8 Safe operating area (2SB1260)

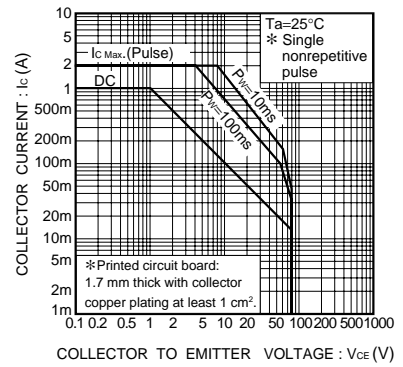


Fig.9 Safe operating area (2SB1241)

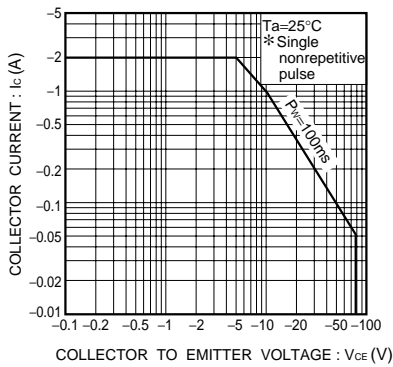


Fig.10 Safe operating area (2SB1181)

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